

INFORMATION DISCLOSURE CITATION

Attorney Docket No.

062020-1440

Applicant
Ayazi, et al.

Filing Date

Serial No.:
10/632,176

Group

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DMK	Α	3,513,356		Newell				6-27-67				
, l	В	3,634,787	1-11-72	Newell		333	72	1-23-68				
	С	5,162,691	11-10-92	Mariani, et al.		310	321	1-22-91				
	D	5,426,070	6-20-95	Shaw, et al.		437	203	5-26-93				
	E	5,491,604	2-13-96	Nguyen, et al.		361	278	12-11-92				
	F	5,587,620	12-24-96	Ruby, et al.		310	346	12-21-93				
	G	5,589,082	12-31-96	Lin, et al.		216	2	6-7-95				
	Н	5,663,505	9-2-97	Nakamura		73	702	5-8-96				
	I	5,719,073	2-17-98	Shaw, et al.		437	228	9-27-94				
	J	5,846,849	12-8-98	Shaw, et al.		438	52	2-24-97				
	К	5,847,454	12-8-98	Shaw, et al.		257	734	9-22-97				
		OTHER DOCU	MENTS (Includ	ding Author, Title, L	ate, Pertinent I	Pages, etc	.)					
DHA	L	Ayazi, et al.; Piezoelectric On Semiconductor-On-Insulator Microelectromechanical Resonators And Methods Of Fabrication; U.S. Patent Application Serial No.10/631,948; filed July 31, 2003										
1	М	Ma, et al.; Sacrificial Lay 2003/0006468 A1; filed Ju		Make Gaps in MEMS	Applications; U	S Patent A	pplication P	ublication No.				
	N	Bourgeois, et al.; Design Monocrystalline Silicon; l										
	0	Mihailovich, et al.; Dissip and Actuators A 50 (1995			ated Single-Cryst	al Silicon	Microresona	tors, Sensors				
	P	Roszhart, et al.; The Effective Solid State Sensor and Ac					Silicon Reso	onators; IEEE				
	Q	Cleland, et al.; Fabricatio Condensed Matter Physics					om Bulk Si C	Crystals;				
	R	No, et al.; The HARPSS F of Nanotechology; Octobe			on Silicon Electro	omechanic	cal Resonator	rs; IEEE Conf				
	S			•	S Water, et al.; "Physical and Structural Properties of ZnO Sputtered Films"; Dept. of EE, National Cheng Kung University; Received May 7, 2001; Pages 67-72							

conformance and not considered. Include copy of this form with next communication to the applicant.

EXAMINER'S SIGNATURE:	1/ /	DATE CONSIDERED:
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DHK	T	5,873,153	2-23-99	Ruby, et al.		29	25.35	8-27-96	
11	U	5,884,378	3-23-99	Dydyk		29	25.35	7-22-96	
	V	5,894,647	4-20-99	Lakin		29	25.35	6-30-97	
	W	5,914,801	6-22-99	Dhuler, et al.		359	230	9-27-96	
	X	5,976,994	11-2-99	Nguyen, et al.		438	795	6-13-97	
	Y	5,998,906	12-7-99	Jerman, et al.		310	309	8-17-98	
	Z	6,000,280	12-14-99	Miller, et al.		73	105	3-23-98	
	a	6,051,866	4-18-00	Shaw, et al.		257	417	8-11-98	
	ь	6,060,818	5-9-00	Ruby, et al.		310	363	6-2-98	
	С	6,067,858	5-30-00	Clark, et al.		73	504.16	5-30-97	
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	j	Abdelmoneum, et al.; Stemi	ess Wine-Glass N	Mode Disk Micromec	hanical Resonators	s; IEEE; 2003	3; pp 698-701		
	k	Piekarski, et al; Surface Mic	romachined Pieze	oelectric Resonant Be	am Filters; Sensor	s and Actuat	ors, A 91; 200	01; pp 313-320	
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. 1	0	6,134,042	10-17-00	Dhuler, et al.		359	224	4-1-99	
	р	6,215,375	4-10-01	Larson, III, et al.		333	187	3-30-99	
	q	6,236,281	5-22-01	Nguyen, et al.		331	154	9-21-99	
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	s	6,239,536	5-29-01	Lakin		310	364	9-8-98	
	t	6,256,134	7-3-01	Dhuler, et al.		359	212	7-28-00	
	u	6,275,122	8-14-01	Speidell, et al.		333	186	8-17-99	
	v	6,275,320	8-14-01	Dhuler, et al.		359	237	9-27-99	
	w	6,291,931	9-18-01	Lakin		310	364	11-23-99	
	х	6,296,779	10-2-01	Clark, et al.		216	66	2-22-99	
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.	z	Ruby, et al.; Ultra-Miniat Circuits Conference; 200			sing FBAR Techno	logy; IEE	E Internation	nal Solid-State	
	AA	Clark, et al.; High-Q VH	F Micromechanic	cal Contour-Mode I	Disk Resonators; IE	EE; 2000;	pp 493-496		
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	FF	No, et al.; Single-Crystal Actuators and Microsyste	ms Workshop; p	p. 281-284, Hilton	Head, SC; June 200)2 			
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. //	MIL	GG	6,348,846	2-19-02	von Gutfeld, et al.		333	201	10-14-99
•	1	НН	6,373,682	4-16-02	Goodwin-Johansson	n	361	278	12-15-99
		11	6,377,438	4-23-02	Deane, et al.		361	278	10-23-00
,		JJ	6,391,674	5-21-02	Ziegler		438	52	12-28-00
		KK	6,428,713	8-6-02	Christenson, et al.		216	2	10-1-99
		LL	6,429,755	8-6-02	Speidell, et al.		333	197	1-30-01
		MM	6,433,401	8-13-02	Clark, et al.		257	524	4-5-00
		NN	6,480,645	11-12-02	Peale, et al.		385	18	1-30-01
		00	6,485,273	11-26-02	Goodwin-Johansson		417	410.2	9-1-00
		PP	6,495,892	12-17-02	Goodman, et al.		257	414	3-26-99
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n	44	RR	Amini, et al.; Capacitive A	ccelerometer; II	EEE International Sc	olid-State Circuits	Conferen	ce; 2000; pp	1-3
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-		ww	Humad, et al.; High Freque	ency Micromech	anical Piezo-On-Sili	con Block Resona	tors; IEEE	E; 2003	
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nnn	XX	6,555,201	4-29-03	Dhuler, et al.			428		137	5-15-00
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	1	077777 70077	(D) 1770 (7 1]	_					
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Mu		Abdolvand, et al.; Thermo				_				
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(ii	Hao, et al.; An Analytical Vibrations; Sensors and A				ined Beam Reso	nators W	ith In	-Plane F	lexural
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